PNZ108 (PN108)

Silicon planar type

For optical control systems

■ Features

- High sensitivity: $I_L = 5 \text{ mA (min.)}$
- Narrow directivity characteristics for effective use of light input
- Fast response: $t_r = 5 \mu s$ (typ.)
- Signal mixing capability using base pin
- TO-18 standard type package

■ Absolute Maximum Ratings $T_a = 25$ °C

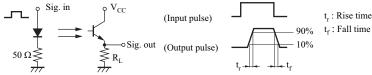
| Parameter | Symbol | Rating | Unit | |
|---------------------------------------|------------------|-------------|------|--|
| Collector-emitter voltage (Base open) | V _{CEO} | 20 | V | |
| Collector-base voltage (Emitter open) | V _{CBO} | 30 | V | |
| Emitter-collector voltage (Base open) | V _{ECO} | 3 | V | |
| Emitter-base voltage (Collector open) | V _{EBO} | 5 | V | |
| Collector current | I_{C} | 30 | mA | |
| Collector power dissipation * | P _C | 150 | mW | |
| Operating ambient temperature | T _{opr} | -25 to +85 | °C | |
| Storage temperature | T _{stg} | -30 to +100 | °C | |

Note) *: The rate of electric power reduction is 1.5 mW/ $^{\circ}$ C above $T_a = 25^{\circ}$ C.

■ Electrical-Optical Characteristics T_a = 25°C±3°C

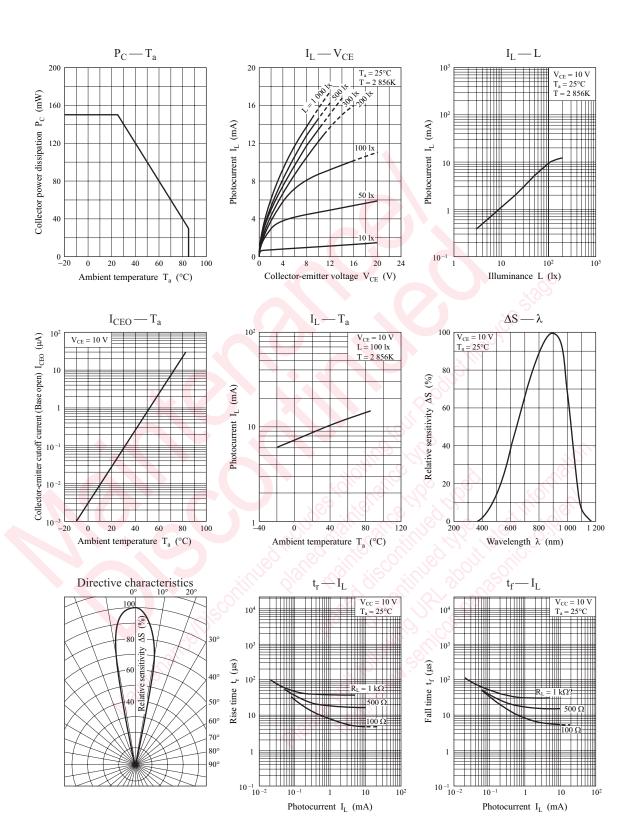
| Parameter | Symbol | Conditions | Min | Тур | Max | Unit |
|--|-------------------------|---|-----|------|-----|------|
| Photocurrent *1 | I_L | $V_{CE} = 10 \text{ V}, L = 100 \text{ lx}$ | 5 | | 15 | mA |
| Collector-emitter cutoff current (Base open) | I_{CEO} | $V_{CE} = 10 \text{ V}$ | 80, | 0.05 | 2.0 | μΑ |
| Collector-emitter saturation voltage *1 | V _{CE(sat)} | $I_L = 1 \text{ mA}, L = 500 \text{ lx}$ | | 0.3 | 0.6 | V |
| Peak sensitivity wavelength | λ_{PD} | $V_{CE} = 10 \text{ V}$ | | 900 | | nm |
| Half-power angle | θ | The angle when the photocurrent is halved | | 10 | | 0 |
| Rise time *2 | $t_{\rm r}$ | V = 10 V I = 5 A D = 100 O | | 5 | | μs |
| Fall time *2 | $t_{\rm f}$ | $V_{CC} = 10 \text{ V}, I_L = 5 \text{ mA}, R_L = 100 \Omega$ | | 6 | | μs |

- Note) 1. Measuring methods are based on JAPANESE INDUSTRIAL STANDARD JIS C 7030 measuring methods for transistors.
 - 2. Spectral sensitivity characteristics: Sensitivity for wave length over 400 nm maximum sensitivity ratio is 100%.
 - 3. This device is designed by disregarding radiation.
 - 4. *1:Source: Tungsten lamp (color temperature 2 856K)
 - *2: Switching time measurement circuit



Note) The part number in the parenthesis shows conventional part number.

PNZ108 Panasonic

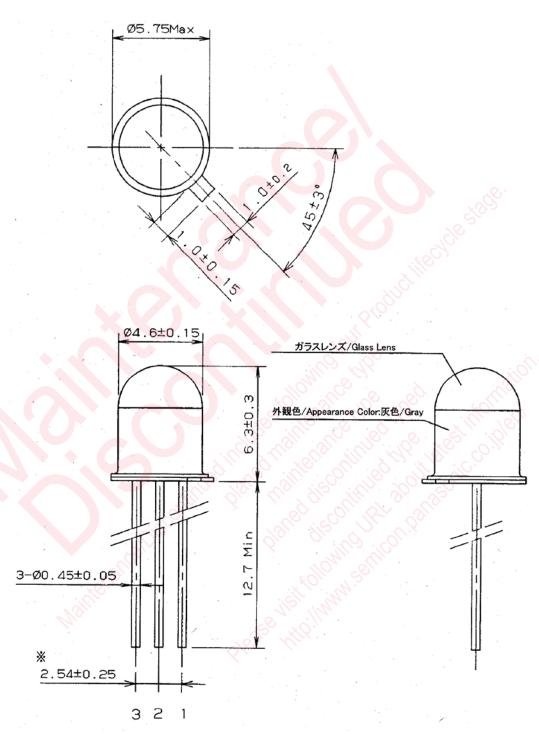


2 SHE00066AEK

Panasonic PNZ108

■ Package (Unit: mm)

MPCLTN3S0001



(注 1)※リード根元寸法とする。/(Note1)※Indicates root dimensions of lead.

- Pin name
 - 1: Emitter
 - 2: Base
 - 3: Collector

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